

**• General Description**

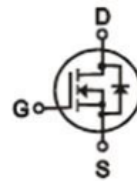
The ZM200N06S combines advanced trench MOSFET technology with a low resistance package to provide extremely low  $R_{DS(ON)}$ .

**• Features**

- Advance high cell density Trench technology
- Low  $R_{DS(ON)}$  to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance

**• Application**

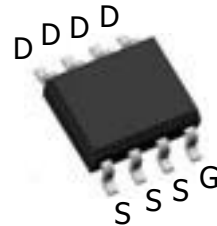
- MB/VGA Vcore
- SMPS 2<sup>nd</sup> Synchronous Rectifier
- POL application
- BLDC Motor driver

**• Product Summary**


$V_{DS} = 60V$

$R_{DS(ON)} = 20m\Omega$

$I_D = 6A$



SOP-8

**• Ordering Information:**

Part NO.	ZM200N06S
Marking	ZM200N06
Packing Information	REEL TAPE
Basic ordering unit (pcs)	4000

**• Absolute Maximum Ratings ( $T_C = 25^\circ C$ )**

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	$V_{DS}$	60	V
Gate-Source Voltage	$V_{GS}$	20	V
Continuous Drain Current	$I_{D@TC=25^\circ C}$	6	A
	$I_{D@TC=75^\circ C}$	4.5	A
	$I_{D@TC=100^\circ C}$	3.8	A
Pulsed Drain Current ①	$I_{DM}$	15	A
Total Power Dissipation	$P_D@TC=25^\circ C$	4.0	W
Total Power Dissipation	$P_D@TA=25^\circ C$	0.75	W
Operating Junction Temperature	$T_J$	-55 to 150	$^\circ C$
Storage Temperature	$T_{STG}$	-55 to 150	$^\circ C$
Single Pulse Avalanche Energy	$E_{AS}$	65	mJ

**•Thermal resistance**

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R <sub>thJC</sub>	-	-	32	° C/W
Thermal resistance, junction - ambient	R <sub>thJA</sub>	-	-	170	° C/W
Soldering temperature, wave soldering for 10s	T <sub>sold</sub>	-	-	265	° C

**•Electronic Characteristics**

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	60			V
Gate Threshold Voltage	V <sub>GS(TH)</sub>	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250uA	1.2		2.5	V
Drain-Source Leakage Current	I <sub>DSS</sub>	V <sub>DS</sub> =60V, V <sub>GS</sub> =0V			1.0	uA
Gate- Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V			±100	nA
Static Drain-source On Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =6A		20	26	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =4A		24	31	mΩ
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =25V, I <sub>D</sub> =5A		14		s
Source-drain voltage	VSD	I <sub>S</sub> =6A			1.28	V

**•Electronic Characteristics**

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	C <sub>iss</sub>	f = 1MHz	-	1650	-	pF
Output capacitance	C <sub>oss</sub>		-	340	-	
Reverse transfer capacitance	C <sub>rss</sub>		-	160	-	

**•Gate Charge characteristics(T<sub>a</sub> = 25°C)**

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Total gate charge	Q <sub>g</sub>	V <sub>DD</sub> = 30V	-	19	-	nC
Gate - Source charge	Q <sub>gs</sub>	I <sub>D</sub> = 3A	-	9	-	
Gate - Drain charge	Q <sub>gd</sub>	V <sub>GS</sub> = 10V	-	11	-	

Note: ① Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2% ;

Fig.1 Power Dissipation

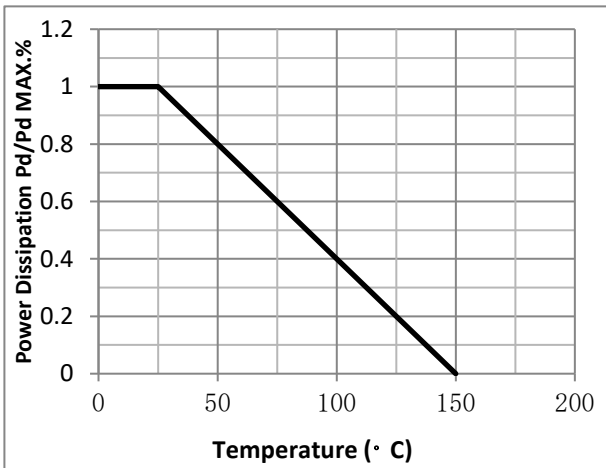


Fig.2 Typical output Characteristics

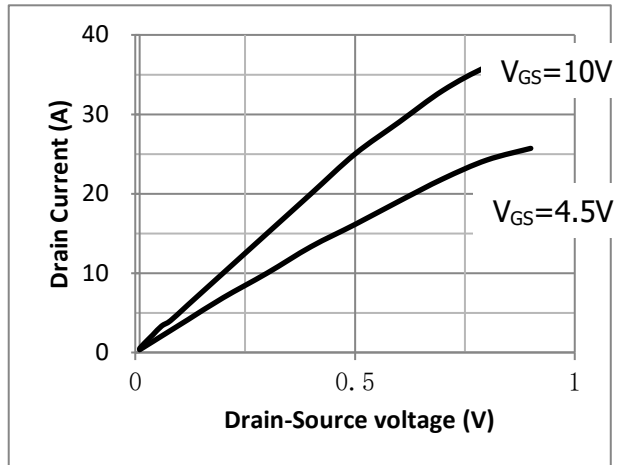


Fig.3 Threshold Voltage V.S Junction Temperature

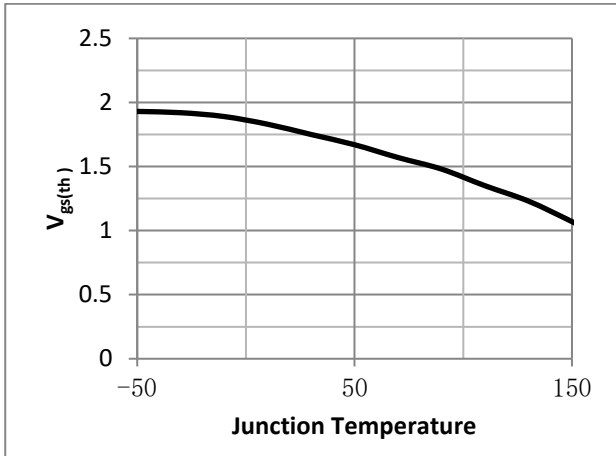


Fig.4 Resistance V.S Drain Current

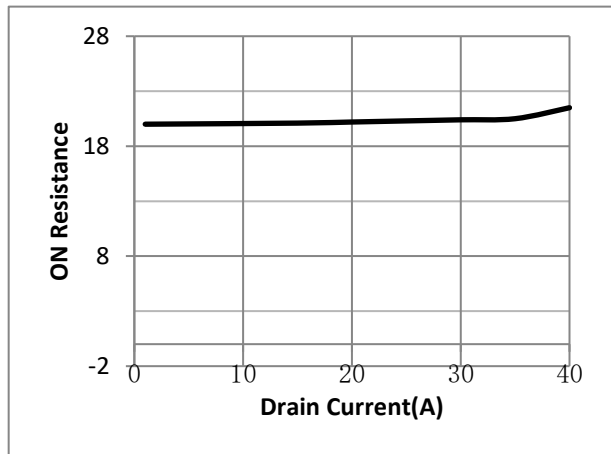


Fig.5 On-Resistance VS Gate Source Voltage

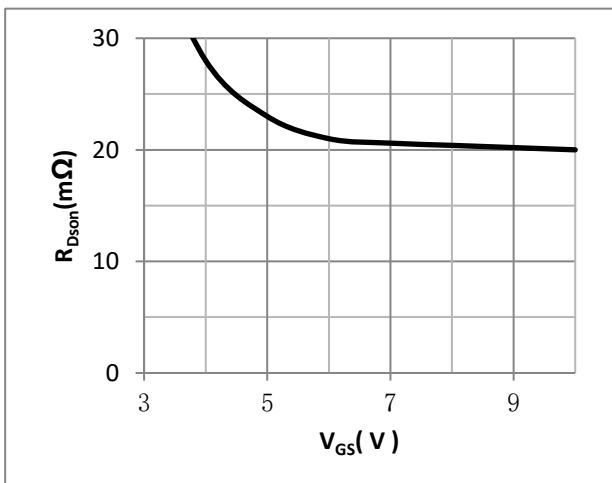


Fig.6 On-Resistance V.S Junction Temperature

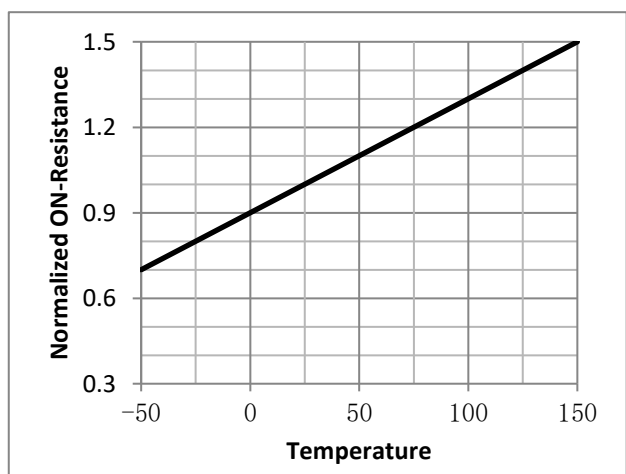


Fig.7 Switching Time Measurement Circuit

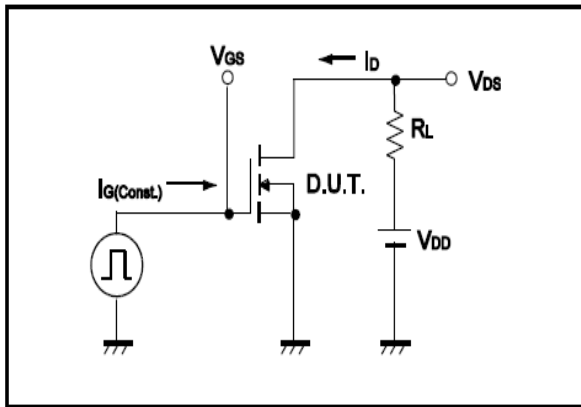


Fig.8 Gate Charge Waveform

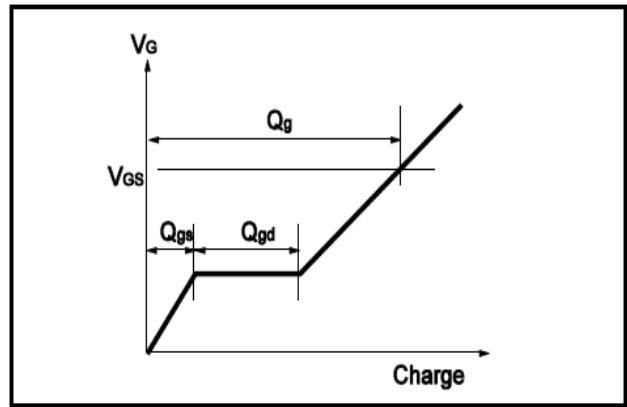


Fig.9 Switching Time Measurement Circuit

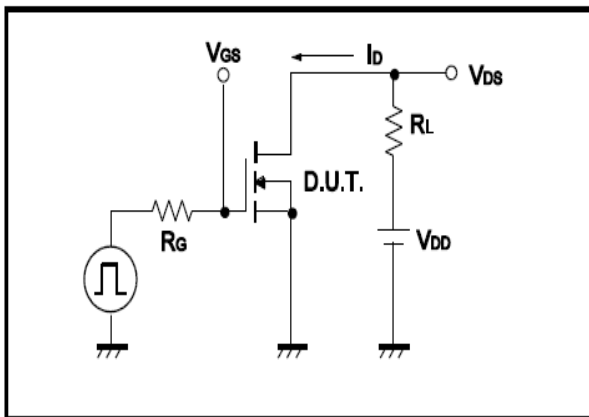


Fig.10 Gate Charge Waveform

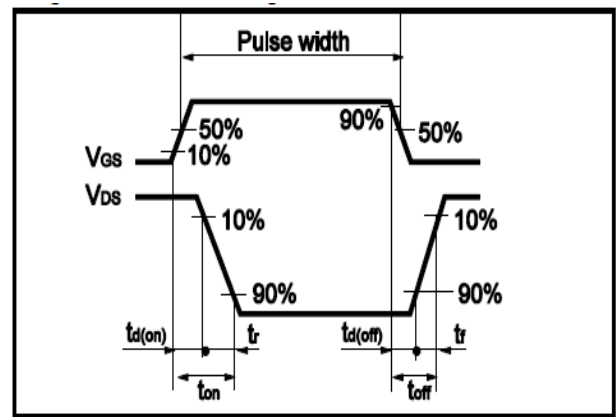


Fig.11 Avalanche Measurement Circuit

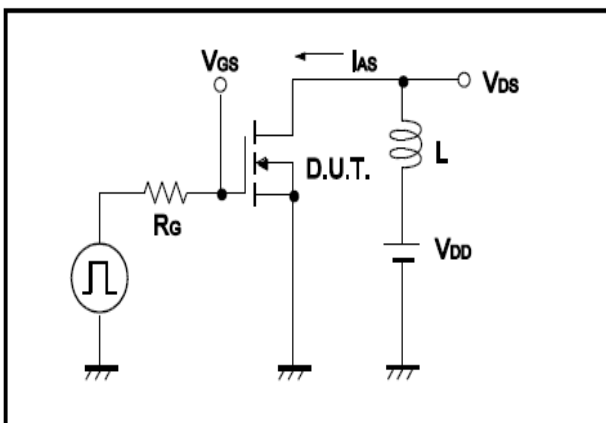
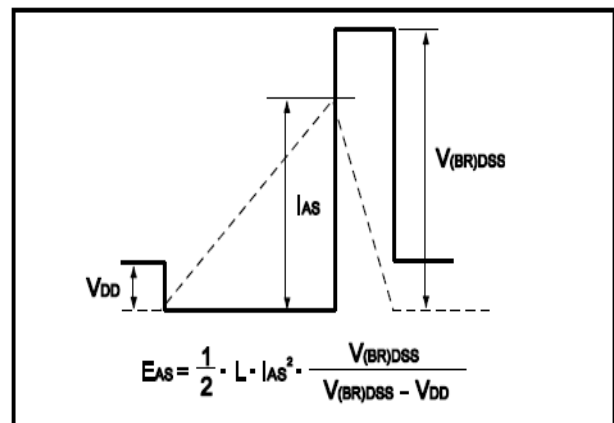


Fig.12 Avalanche Waveform





•Dimensions(SOP8)

Unit: mm

SYMBOL	min	TYP	max	SYMBOL	min		max
A	4.80		5.25	C	1.30		1.75
A1	0.37		0.49	C1	0.55		0.75
A2		1.27		C2	0.55		0.65
A3		0.41		C3	0.05		0.20
B	5.80		6.20	C4	0.10	0.20	0.23
B1	3.80		4.10	D		1.05	
B2		5.00		D1	0.40		0.62

